INTEGRATED CIRCUITS

DATA SHEET

For a complete data sheet, please also download:

- The IC06 74HC/HCT/HCU/HCMOS Logic Family Specifications
- The IC06 74HC/HCT/HCU/HCMOS Logic Package Information
- The IC06 74HC/HCT/HCU/HCMOS Logic Package Outlines

74HC/HCT6704 x 4 register file; 3-state

Product specification
File under Integrated Circuits, IC06

December 1990

Philips Semiconductors





74HC/HCT670

FEATURES

- Simultaneous and independent read and write operations
- Expandable to almost any word size and bit length
- · Output capability: bus driver
- · I_{CC} category: MSI

GENERAL DESCRIPTION

The 74HC/HCT670 are high-speed Si-gate CMOS devices and are pin compatible with low power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard no. 7A.

The 74HC/HCT670 are 16-bit 3-state register files organized as 4 words of 4 bits each. Separated read and write address inputs (R_A , R_B and W_A , W_B) and enable inputs (\overline{RE} and \overline{WE}) are available, permitting simultaneous writing into one word location and reading from another location. The 4-bit word to be stored is presented to four data inputs (D_0 to D_3). The W_A and W_B inputs determine

the location of the stored word. When the \overline{WE} input is LOW, the data is entered into the addressed location. The addressed location remains transparent to the data while the \overline{WE} input is LOW. Data supplied at the inputs will be read out in true (non-inverting) form from the 3-state outputs (Q₀ to Q₃). D_n and W_n inputs are inhibited when \overline{WE} is HIGH.

Direct acquisition of data stored in any of the four registers is made possible by individual read address inputs (R_A and R_B). The addressed word appears at the four outputs when the $\overline{\text{RE}}$ is LOW. Data outputs are in the high impedance OFF-state when $\overline{\text{RE}}$ is HIGH. This permits outputs to be tied together to increase the word capacity to very large numbers.

Design of the read enable signals for the stacked devices must ensure that there is no overlap in the LOW levels which would cause more than one output to be active at the same time. Parallel expansion to generate n-bit words is accomplished by driving the enable and address inputs of each device in parallel.

QUICK REFERENCE DATA

 $GND = 0 \text{ V}; T_{amb} = 25 \, ^{\circ}\text{C}; t_r = t_f = 6 \text{ ns}$

SYMBOL	PARAMETER	CONDITIONS	TYP	UNIT	
STIVIBUL	PARAMETER	CONDITIONS	НС	нст	UNII
t _{PHL} / t _{PLH}	propagation delay D _n to Q _n	C _L = 15 pF; V _{CC} = 5 V	23	23	ns
Cı	input capacitance		3.5	3.5	pF
C _{PD}	power dissipation capacitance per package	notes 1 and 2	122	124	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

$$P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$$
 where:

f_i = input frequency in MHz

f_o = output frequency in MHz

 $\sum (C_L \times V_{CC}^2 \times f_0) = \text{sum of outputs}$

C_I = output load capacitance in pF

 V_{CC} = supply voltage in V

2. For HC the condition is $V_I = GND$ to V_{CC} ; for HCT the condition is $V_I = GND$ to $V_{CC} - 1.5$ V

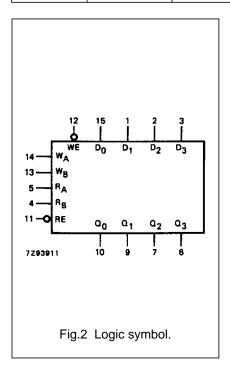
ORDERING INFORMATION

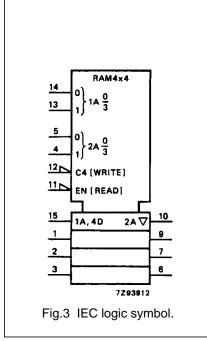
See "74HC/HCT/HCU/HCMOS Logic Package Information".

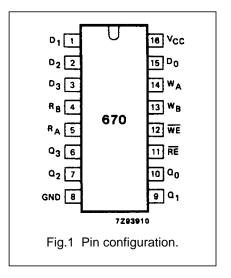
74HC/HCT670

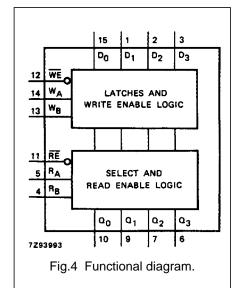
PIN DESCRIPTION

PIN NO.	SYMBOL	NAME AND FUNCTION
5, 4	R _A , R _B	read address inputs
8	GND	ground (0 V)
10, 9, 7, 6	Q ₀ to Q ₃	data outputs
11	RE	3-state output read enable input (active LOW)
12	WE	write enable input (active LOW)
14, 13	W _A , W _B	write address inputs
15, 1, 2, 3	D ₀ to D ₃	data inputs
16	V _{CC}	positive supply voltage









WRITE MODE SELECT TABLE

OPERATING	INP	UTS	INTERNAL				
MODE	WE	D _n	LATCHES ⁽¹⁾				
write data	L	L	L				
write data	L	Н	Н				
data latched	Н	Х	no change				

Note

1. The write address (W_A and W_B) to the "internal latches" must be stable while \overline{WE} is LOW for conventional operation.

READ MODE SELECT TABLE

OPERATING		OUTPUT			
MODE	RE	INTERNAL LATCHES(1)	Q _n		
rood.	L	L	L		
read	L	Н	Н		
disabled	Н	Х	Z		

Notes

1. The selection of the "internal latches" by read address (R_A and R_B) are not constrained by \overline{WE} or \overline{RE} operation.

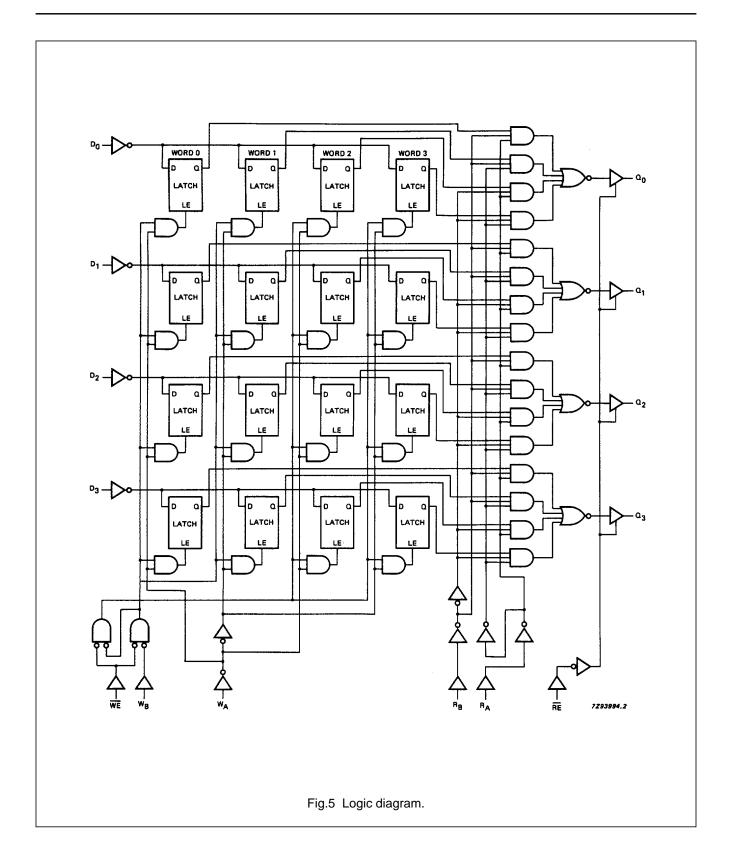
H = HIGH voltage level

L = LOW voltage level

X = don't care

Z = high impedance OFF-state

74HC/HCT670



Philips Semiconductors Product specification

4 x 4 register file; 3-state

74HC/HCT670

DC CHARACTERISTICS FOR 74HC

For the DC characteristics see "74HC/HCT/HCU/HCMOS Logic Family Specifications".

Output capability: bus driver

I_{CC} category: MSI

AC CHARACTERISTICS FOR 74HC

 $GND = 0 V; t_r = t_f = 6 ns; C_L = 50 pF$

	PARAMETER	T _{amb} (°C)								TEST CONDITIONS	
SYMBOL		74HC									
STWIBOL		+25			-40 to +85		-40 to+125		UNIT	V _{CC}	WAVEFORMS
		min.	typ.	max.	min.	max.	min.	max.		(-,	
t _{PHL} / t _{PLH}	propagation delay R _A , R _B to Q _n		58 21 17	195 39 33		245 49 42		295 59 50	ns	2.0 4.5 6.0	Fig.6
t _{PHL} / t _{PLH}	propagation delay WE to Q _n		77 28 22	250 50 43		315 63 54		375 75 64	ns	2.0 4.5 6.0	Fig.7
t _{PHL} / t _{PLH}	propagation delay D _n to Q _n		74 27 22	250 50 43		315 63 54		375 75 64	ns	2.0 4.5 6.0	Fig.7
t _{PZH} / t _{PZL}	3-state output enable time RE to Q _n		39 14 11	150 30 26		190 38 33		225 45 38	ns	2.0 4.5 6.0	Fig.9
t _{PHZ} / t _{PLZ}	3-state output disable time RE to Q _n		47 17 14	150 30 26		190 38 33		225 45 38	ns	2.0 4.5 6.0	Fig.9
t _{THL} / t _{TLH}	output transition time		14 5 4	60 12 10		75 15 13		90 18 15	ns	2.0 4.5 6.0	Fig.6
t _W	write enable pulse width LOW	80 16 14	14 5 4		100 20 17		120 24 20		ns	2.0 4.5 6.0	Fig.8
t _{su}	set-up time D _n to WE	60 12 10	3 1 1		75 15 13		90 18 15		ns	2.0 4.5 6.0	Fig.8
t _{su}	set-up time W _A , W _B to WE	60 12 10	6 2 2		75 15 13		90 18 15		ns	2.0 4.5 6.0	Fig.8
t _h	hold time D _n to WE	5 5 5	0 0 0		5 5 5		5 5 5		ns	2.0 4.5 6.0	Fig.8
t _h	hold time W _A , W _B to WE	5 5 5	0 0 0		5 5 5		5 5 5		ns	2.0 4.5 6.0	Fig.8
t _{latch}	latch time WE to R _A , R _B	100 20 17	28 10 8		125 25 21		150 30 26		ns	2.0 4.5 6.0	Fig.8

December 1990

Philips Semiconductors Product specification

4 x 4 register file; 3-state

74HC/HCT670

DC CHARACTERISTICS FOR 74HCT

For the DC characteristics see "74HC/HCT/HCU/HCMOS Logic Family Specifications".

Output capability: bus driver

I_{CC} category: MSI

Note to HCT types

The value of additional quiescent supply current (ΔI_{CC}) for a unit load of 1 is given in the family specifications. To determine ΔI_{CC} per input, multiply this value by the unit load coefficient shown in the table below.

6

INPUT	UNIT LOAD COEFFICIENT
D _n	0.25
WE, WA	0.40
W _B	0.60
R _A	0.70
R _B RE	1.10
RE	1.35

74HC/HCT670

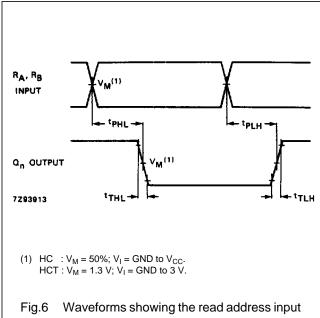
AC CHARACTERISTICS FOR 74HCT

 $GND = 0 V; t_r = t_f = 6 ns; C_L = 50 pF$

	PARAMETER	T _{amb} (°C)								TEST CONDITIONS	
SYMBOL		74HCT									
		+25			-40 to +85		-40 to +125		UNIT	V _{CC} (V)	WAVEFORMS
		min.	typ.	max.	min.	max.	min.	max.		(*)	
t _{PHL} / t _{PLH}	propagation delay R _A , R _B to Q _n		21	40		50		60	ns	4.5	Fig.6
t _{PHL} / t _{PLH}	propagation delay WE to Q _n		28	50		63		75	ns	4.5	Fig.7
t _{PHL} / t _{PLH}	propagation delay D _n to Q _n		27	50		63		75	ns	4.5	Fig.7
t _{PZH} / t _{PZL}	3-state output enable time RE to Q _n		18	35		44		53	ns	4.5	Fig.9
t _{PHZ} / t _{PLZ}	3-state output disable time RE to Q _n		19	35		44		53	ns	4.5	Fig.9
t _{THL} / t _{TLH}	output transition time		5	12		15		18	ns	4.5	Fig.6
t _W	write enable pulse width LOW	18	9		23		27		ns	4.5	Fig.8
t _{su}	set-up time D _n to WE	12	4		15		18		ns	4.5	Fig.8
t _{su}	set-up time $\overline{W_A}$, W_B to \overline{WE}	12	-2		15		18		ns	4.5	Fig.8
t _h	hold time D _n to WE	5	-1		5		5		ns	4.5	Fig.8
t _h	hold time W _A , W _B to WE	5	0		5		5		ns	4.5	Fig.8
t _{latch}	latch time WE to R _A , R _B	25	11		31		38		ns	4.5	Fig.8

74HC/HCT670

AC WAVEFORMS



D_n INPUT $Q_n \text{ OUTPUT}$ $V_M^{(1)}$ $V_M^{(1)}$

pulse width.

Fig.6 Waveforms showing the read address input (R_A, R_B) to output (Q_n) propagation delays and output transition times.

(1) HC: V_M = 50%; V_I = GND to V_{CC}.
HCT: V_M = 1.3 V; V_I = GND to 3 V.

The shaded areas indicate when the input is permitted to change for predictable output performance.

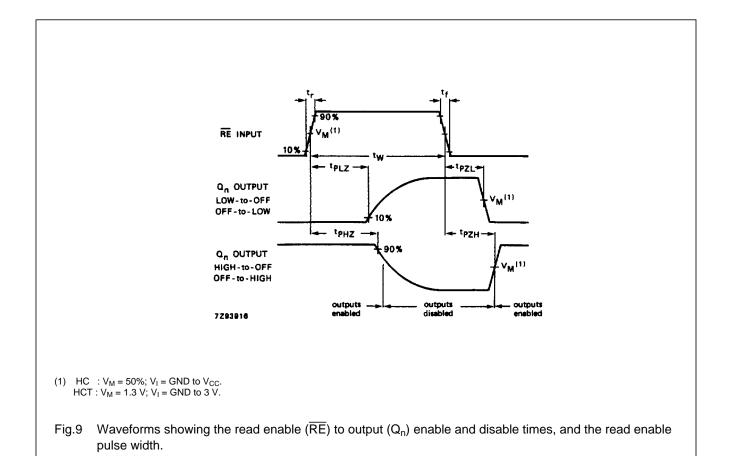
The time allowed for the internal output of the latch to assume the state of the new data (I_{statch}) is important only when attempting to read from a location immediately after that location has received new data. This parameter is measured from the falling edge of WE to the rising edge of R_A or R_B, RE must be LOW.

R_A, R_B
INPUT

T283915.1

Fig.8 Waveforms showing the write address input (W_A, W_B) and data input (D_n) to write enable (\overline{WE}) set-up, hold and latch times.

74HC/HCT670



PACKAGE OUTLINES

See "74HC/HCT/HCU/HCMOS Logic Package Outlines".